

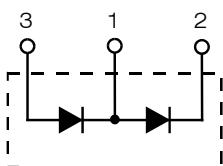
Diode Modules

PSKD 44

Preliminary Data Sheet

I_{FRMS} = 2x 100 A
I_{FAVM} = 2x 64 A
V_{RRM} = 800-1800 V

V _{RSM} V	V _{RRM} V	Type
900	800	PSKD 44/08
1300	1200	PSKD 44/12
1500	1400	PSKD 44/14
1700	1600	PSKD 44/16
1900	1800	PSKD 44/18



Symbol	Test Conditions	Maximum Ratings	
I _{FRMS}	T _{VJ} = T _{VJM}	100	A
I _{FAVM}	T _C = 92°C; 180° sine	64	A
	T _C = 100°C; 180° sine	59	A
I _{FSM}	T _{VJ} = 45°C; V _R = 0	1150	A
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1300	A
	T _{VJ} = T _{VJM} V _R = 0	1000	A
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1200	A
∫i ² dt	T _{VJ} = 45°C V _R = 0	6600	A ² s
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	7000	A ² s
	T _{VJ} = T _{VJM} V _R = 0	5000	A ² s
	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	5950	A ² s
T _{VJ}		-40...+150	°C
T _{VJM}		150	°C
T _{stg}		-40...+125	°C
V _{ISOL}	50/60 Hz, RMS	3000	V~
	I _{ISOL} ≤ 1 mA	3600	V~
M _d	Mounting torque (M5) Terminal connection torque (M5)	2.5-4/22-35 Nm/lb.in.	
		2.5-4/22-35 Nm/lb.in.	
Weight	Typical including screws	90	g
Symbol	Test Conditions	Characteristic Values	
I _R	T _{VJ} = T _{VJM} ; V _R = V _{RRM}	10	mA
V _F	I _F = 200 A; T _{VJ} = 25°C	1.60	V
V _{TO}	For power-loss calculations only	0.8	V
r _T	T _{VJ} = T _{VJM}	4.3	mΩ
Q _S	T _{VJ} = 125°C; I _F = 50 A, -di/dt = 0.64 A/μs	90	μC
I _{RM}		11	A
R _{thJC}	per diode; DC current	0.59	K/W
	per module	0.295	K/W
R _{thJK}	per diode; DC current	0.79	K/W
	per module	0.395	K/W
d _s	Creepage distance on surface	12.7	mm
d _A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

Features

- International standard package JEDEC TO-240 AA
- Direct copper bonded Al₂O₃ -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 148688

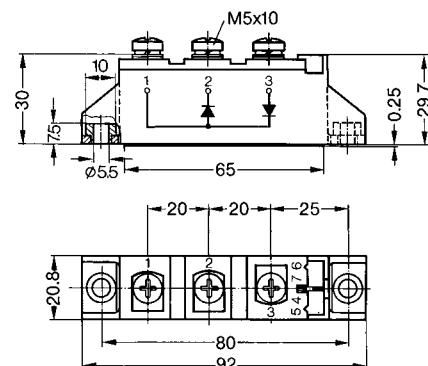
Applications

- Supplies for DC power equipment
- DC supply for PWM inverter
- Field supply for DC motors
- Battery DC power supplies

Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

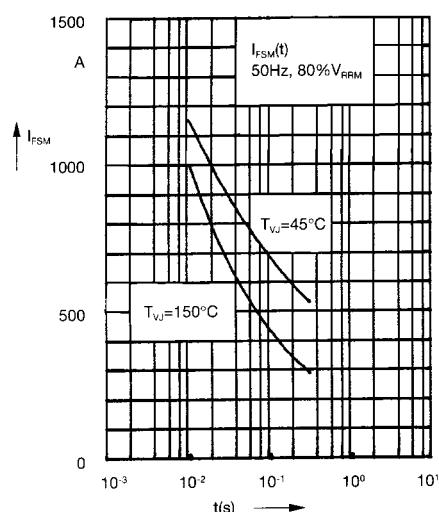


Fig. 1 Surge overload current
 I_{FSM} : Crest value, t : duration

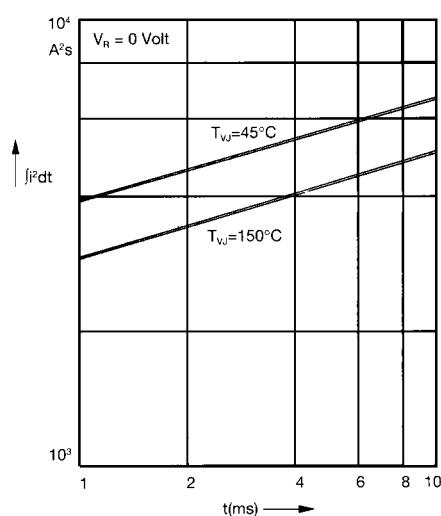


Fig. 2 $\int i^2 dt$ versus time (1-10 ms)

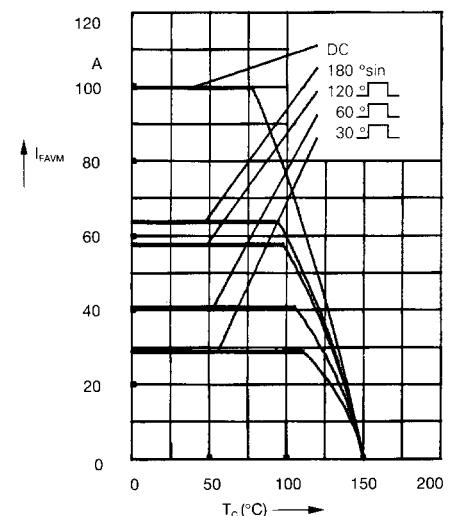


Fig. 2a Maximum forward current
at case temperature

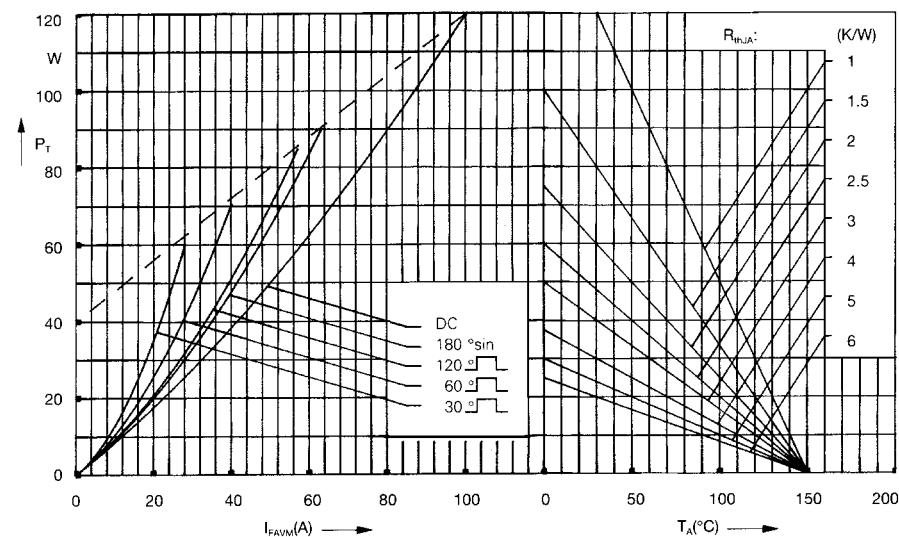


Fig. 3 Power dissipation versus
forward current and ambient
temperature (per diode)

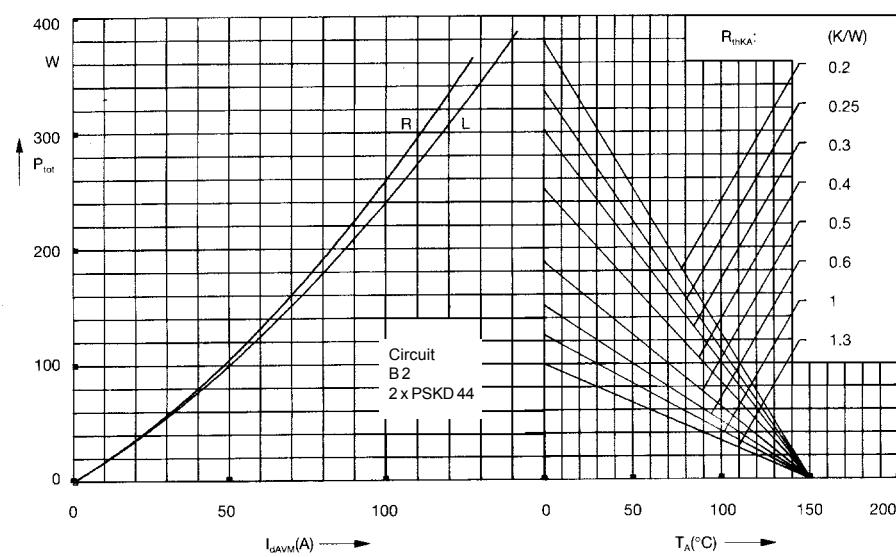


Fig. 4 Single phase rectifier bridge:
Power dissipation versus direct
output current and ambient
temperature
R = resistive load
L = inductive load

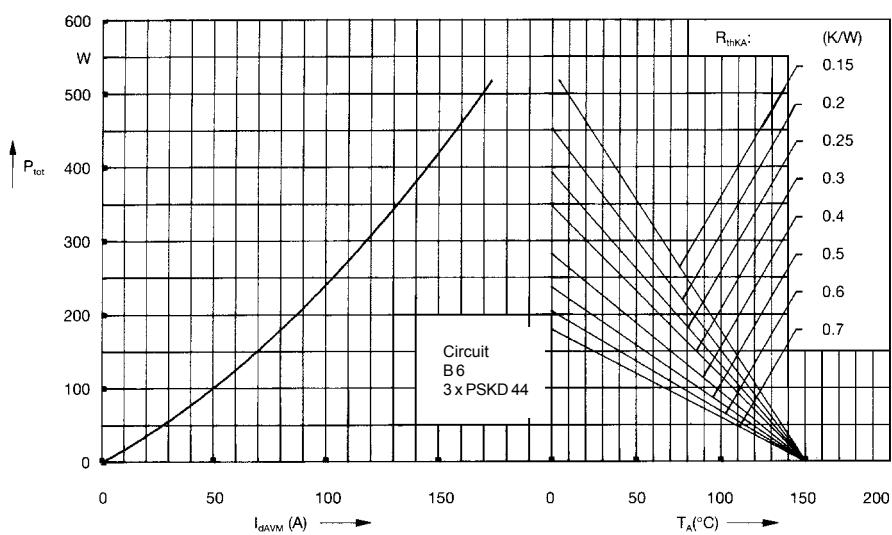


Fig. 5 Three phase rectifier bridge:
Power dissipation versus direct
output current and ambient
temperature

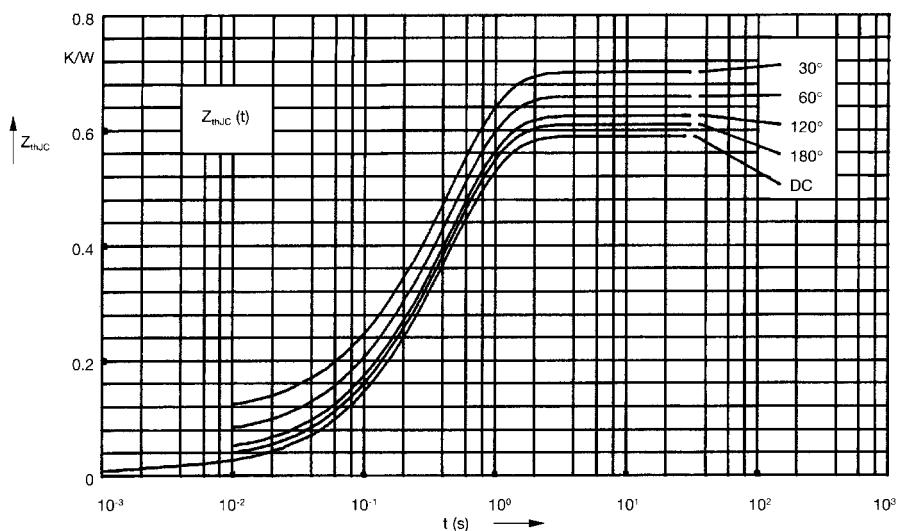


Fig. 6 Transient thermal impedance
junction to case (per diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.59
180°	0.61
120°	0.63
60°	0.66
30°	0.70

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.012	0.0012
2	0.045	0.095
3	0.533	0.455

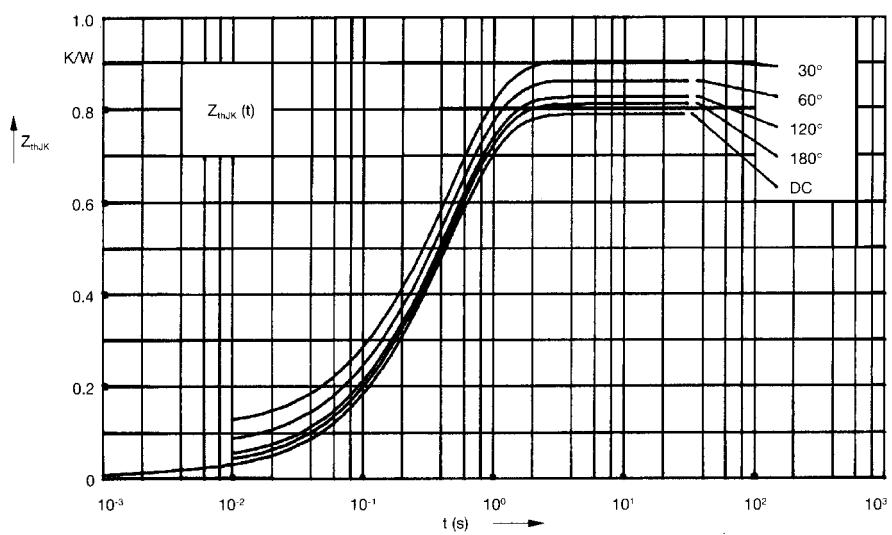


Fig. 7 Transient thermal impedance
junction to heatsink (per diode)

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.79
180°	0.81
120°	0.83
60°	0.86
30°	0.90

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.012	0.0012
2	0.045	0.095
3	0.533	0.455
4	0.2	0.495